

2023 IEEE International Meeting for Future of Electron Devices, Kansai (IMFEDK 2023)

**Kyoto, Japan
16-17 November 2023**



**IEEE Catalog Number: CFP23567-POD
ISBN: 979-8-3503-9379-8**

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IEEE Catalog Number:	CFP23567-POD
ISBN (Print-On-Demand):	979-8-3503-9379-8
ISBN (Online):	979-8-3503-9378-1
ISSN:	2836-9955

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